ABSTRACT OF THE DISCLOSURE

A method of fabricating a semiconductor device according to the invention comprises forming a capacitor comprising a lower electrode formed on a semiconductor substrate, a capacitive insulator made up of a metal oxide film, formed on the lower electrode, and an upper electrode formed on the capacitive insulator; forming a metal pattern to be electrically connected to the electrodes of the capacitor; forming a first protection film which coats at least a side face of the metal pattern; and forming a water constituents diffusion preventive film on the side face and top face of the metal pattern through the intermediary of the first protection film. As a result, a method of fabricating a ferroelectric memory capable of protecting a ferroelectric capacitor from water constituents evolved during a fabrication process, and maintaining satisfactory memory characteristics can be provided.